

Chip-Integrated Full-Stokes Polarimetric Imaging Sensor

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We report a chip-integrated, dual-wavelength (red: 630-670 nm and cyan: 480-520nm) full Stokes polarimetric complementary metal-oxide-semiconductor (CMOS) imaging sensor based on sub-wavelength scale metasurface polarization filter arrays (MPFA). MPFA composes of 168×56 full Stokes filter units (Fig. 1A), each consists of four linear polarization (LP) filters and two sets of chiral metasurface (CM). As illustrated (Fig. 1B), amorphous silicon (a-Si) nano gratings (top) were designed to introduce artificial birefringence that converts circularly polarized light (CPL) to linearly polarized light (LPL)¹. The LPL is further filtered by LP gratings (bottom). Our CM design has a unique dual-color use, achieving a maximum circularly polarized light extinction ratio (CPLER) over 600 with a transmission efficiency of 61.5 % at 650 nm and a CPLER of 170 with an efficiency of 24.5 % at 510 nm. Moreover, this design can operate over a broad wavelength range of 600nm to 700 nm and 450nm to 525 nm with a CPLER over 10, with the bandwidth comparable to grating diffraction-based designs².

The key device fabrication steps are shown in figure 1C: First, nano-gratings with period of 297nm and 90nm of width was patterned by electron beam lithography (EBL) onto 130nm thick a-Si thin films deposited on fused silica substrate by Plasma Enhanced Chemical Vapor Deposition (PECVD), followed by inductively coupled plasma (ICP) etching of a-Si to form a-Si gratings. 520nm thick SiO_x spacer layer was then sputter-deposited onto a-Si gratings by physical vapor deposition (PVD), followed by a second EBL to pattern gratings with duty cycle of 50% and period of 210nm on SiO_x spacer layer. Then the spacer layer was etched by 110nm via reactive ion etching (RIE) etching, followed by electron-beam evaporation of 80nm thick aluminum (Al), leaving 30nm gap in between top and bottom Al double layer grating for near field coupling. 200nm of SiO_x capping layer was then sputtered onto double layer grating. Finally, we spin coated ultraviolet light (UV) resist onto a commercial CMOS sensor (IMX477) and use homemade transfer setup to align and bond the MPFA onto the CMOS sensor. Using the packaged sensor, 7 polarization states were measured at both the red and cyan wavelengths, the average measurement error of S1, S2, S3 were measured

¹ Basiri, A., et al., *Nature-inspired chiral metasurfaces for circular polarization detection and full-Stokes polarimetric measurements*. *Light: Science & Applications*, 2019. **8**(1): p. 1-11.

² Rubin, N.A., et al., *Polarization state generation and measurement with a single metasurface*. *Optics express*, 2018. **26**(17): p. 21455-21478.

less than 2% for red and 3% for cyan, which is much lower than the state of the art diffraction grating based design². The exemplary full Stokes polarization images show images of logo of Arizona State University (ASU) made of LP films with a quarter-wave plate (QWP) in optical path to convert logo 'fork' and 'S' into CP light, as shown in the degree of circular polarization (DOCP) image in Figure 1D-a. In addition, the birefringence induced by internal stress of a plastic protractor causing highly non-uniform DOCP and angle of polarization (AOP) images is shown in Figure 1D-b. Our sensor could be widely adopted in applications requiring polarization information for sensing and imaging such as enhanced small object (e.g., mirror defects) detection in solar power plants, remote sensing , biomedical imaging, etc.

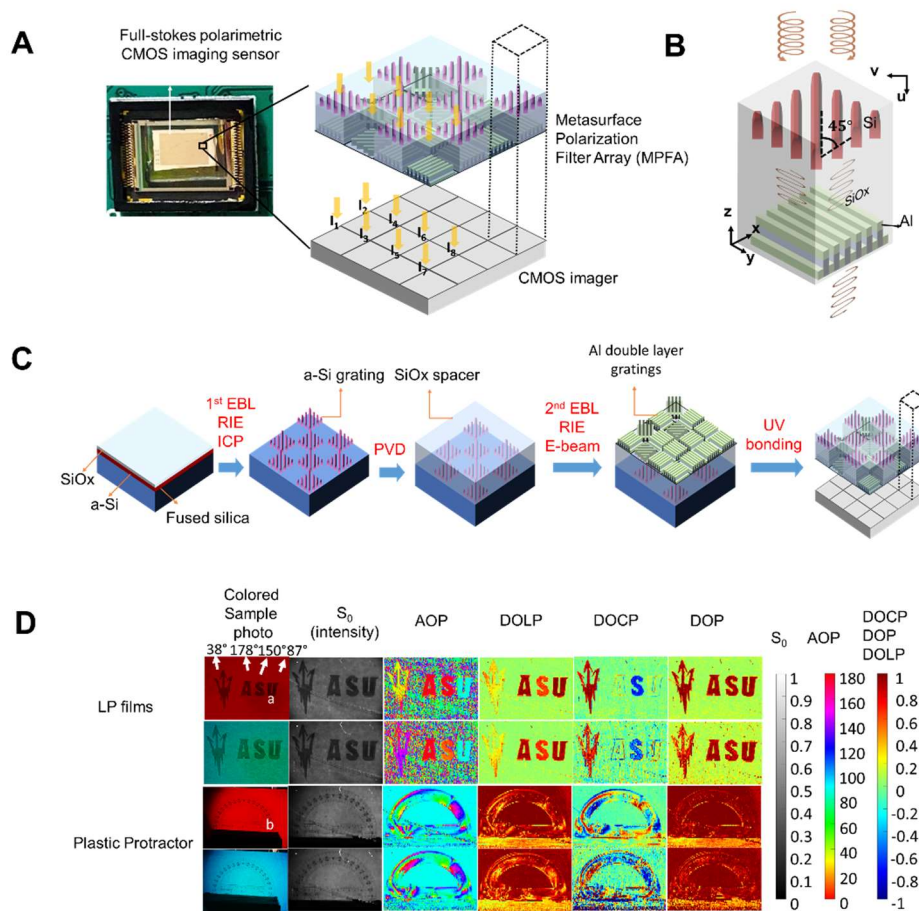


Figure.1 Design concept, full Stokes polarization detection, and polarization imaging. (A) The design concept of full Stokes polarization imaging sensor. I_1, I_5 denotes transmitted intensity of right handed circularly polarized (RCP) component of incoming light. Likewise I_4, I_8 corresponds to left handed circularly polarized (LCP) component, I_2, I_3, I_6, I_7 corresponds to $45^\circ, 135^\circ, 90^\circ, 0^\circ$ LP component. (B) 3D schematic of the chiral metasurface (C) Fabrication process of the MPFA (D). Full Stokes parameter polarization imaging of objects under red and cyan light illumination. a: LP films cut into Arizona State University logo, each with polarization axis $38^\circ, 178^\circ, 150^\circ, 87^\circ$ respectively. b. plastic protractor with 0° LP as input background. S_0 : intensity of the image. AOP: angle of polarization; DOLP: degree of linear polarization; DOCP: degree of circular polarization; DOP: degree of polarization;